

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (π -MOSIII)

2SK2608

HIGH SPEED, HIGH VOLTAGE SWITCHING APPLICATIONS
SWITCHING REGULATOR APPLICATIONS

- Low Drain-Source ON Resistance : $R_{DS(ON)}=3.73\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}|=2.6S$ (Typ.)
- Low Leakage Current : $I_{DSS}=100\mu A$ (Max.) ($V_{DS}=720V$)
- Enhancement-Mode : $V_{th}=2.0\sim 4.0V$ ($V_{DS}=10V$, $I_D=1mA$)

MAXIMUM RATINGS ($T_a=25^{\circ}C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	900	V
Drain-Gate Voltage ($R_{GS}=20k\Omega$)		V_{DGR}	900	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	DC	I_D	3	A
	Pulse	I_{DP}	9	A
Drain Power Dissipation ($T_c=25^{\circ}C$)		P_D	100	W
Single Pulse Avalanche Energy**		E_{AS}	295	mJ
Avalanche Current		I_{AR}	3	A
Repetitive Avalanche Energy*		E_{AR}	10.0	mJ
Channel Temperature		T_{ch}	150	$^{\circ}C$
Storage Temperature Range		T_{stg}	$-55\sim 150$	$^{\circ}C$

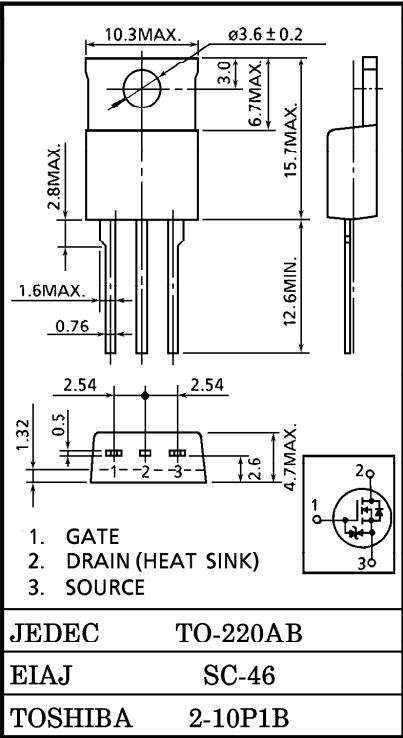
THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	1.25	$^{\circ}C/W$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	83.3	$^{\circ}C/W$

- Note ;
- * Repetitive rating ; Pulse Width Limited by Max. junction temperature.
 - ** $V_{DD}=90V$, $T_{ch}=25^{\circ}C$, $L=60.0mH$, $R_G=25\Omega$, $I_{AR}=3A$

THIS TRANSISTOR IS AN ELECTROSTATIC SENSITIVE DEVICE.
PLEASE HANDLE WITH CAUTION.

INDUSTRIAL APPLICATIONS
Unit in mm

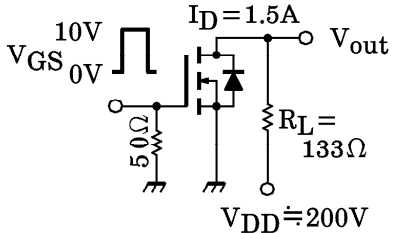


Weight : 2.0g

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

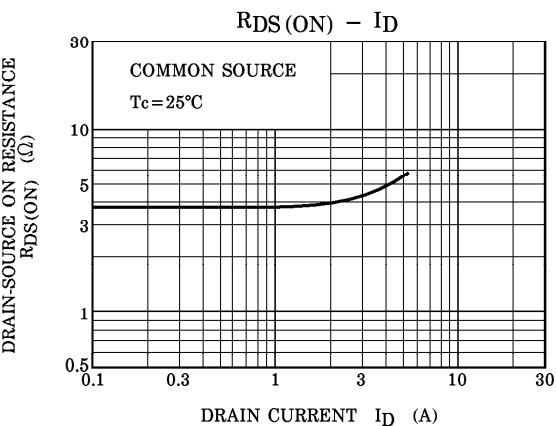
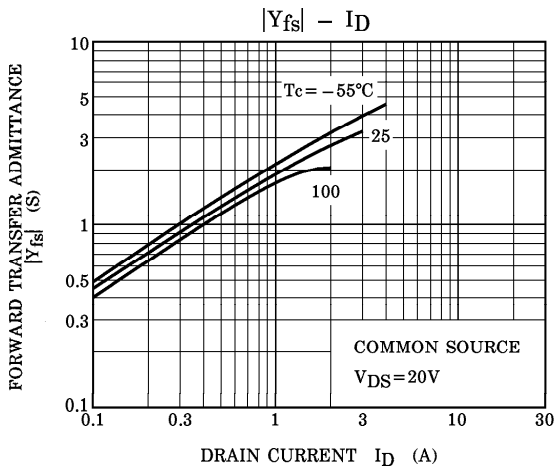
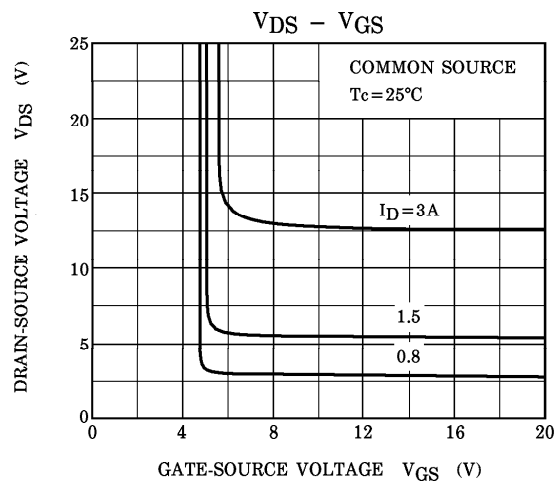
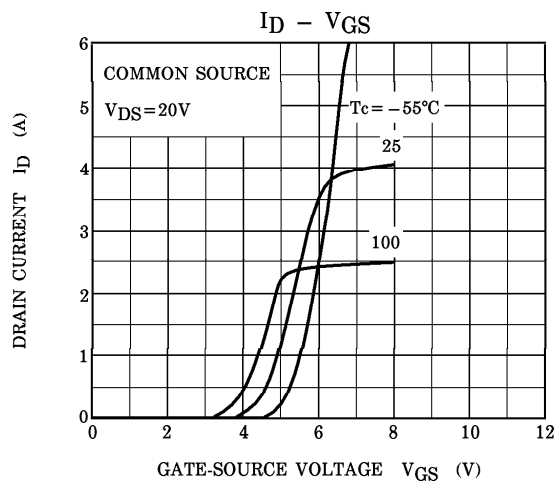
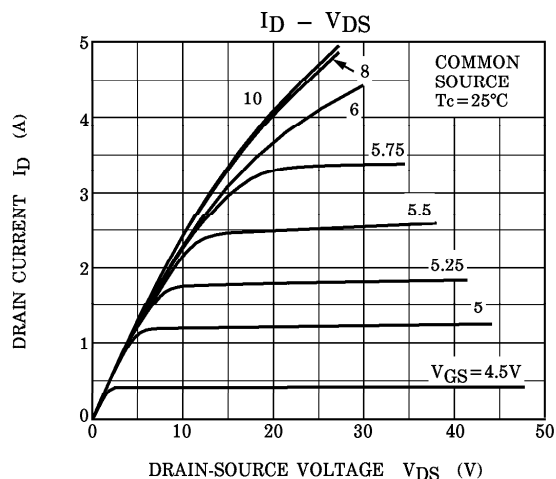
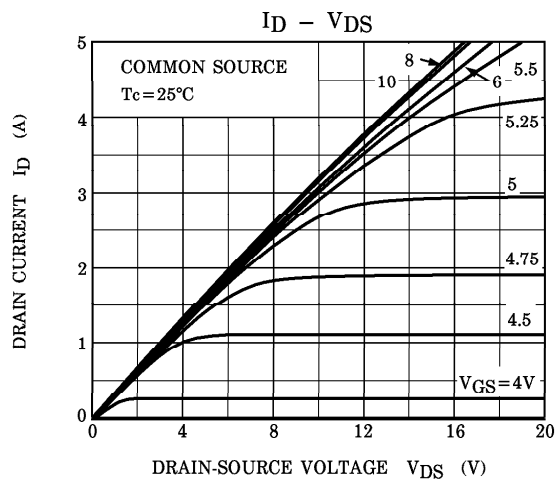
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS} = \pm 30V, V_{DS} = 0V$	—	—	± 10	μA
Gate-Source Breakdown Voltage		$V_{(BR) GSS}$	$I_G = \pm 10\mu A, V_{DS} = 0V$	± 30	—	—	V
Drain Cut-off Current		I_{DSS}	$V_{DS} = 720V, V_{GS} = 0V$	—	—	100	μA
Drain-Source Breakdown Voltage		$V_{(BR) DSS}$	$I_D = 10mA, V_{GS} = 0V$	900	—	—	V
Gate Threshold Voltage		V_{th}	$V_{DS} = 10V, I_D = 1mA$	2.0	—	4.0	V
Drain-Source ON Resistance		$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 1.5A$	—	3.73	4.3	Ω
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = 20V, I_D = 1.5A$	0.65	2.6	—	S
Input Capacitance		C_{iss}	$V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$	—	750	—	pF
Reverse Transfer Capacitance		C_{rss}		—	10	—	
Output Capacitance		C_{oss}		—	70	—	
Switching Time	Rise Time	t_r		—	15	—	ns
	Turn-on Time	t_{on}		—	55	—	
	Fall Time	t_f		—	30	—	
	Turn-off Time	t_{off}		—	110	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q_g	$V_{DD} \doteq 400V, V_{GS} = 10V, I_D = 3A$	—	25	—	nC
Gate-Source Charge		Q_{gs}		—	13	—	
Gate-Drain ("Miller") Charge		Q_{gd}		—	12	—	

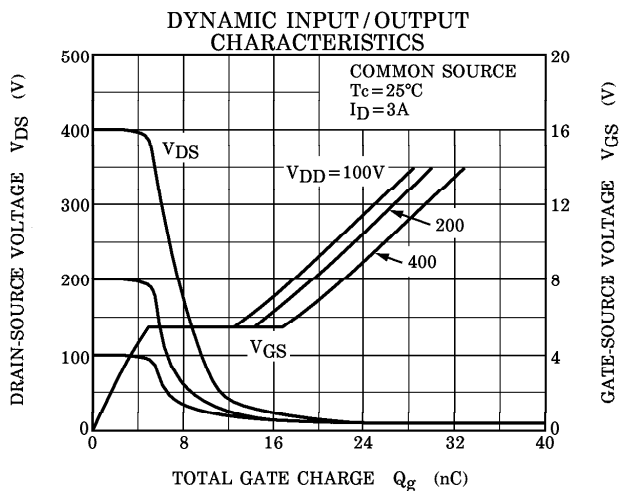
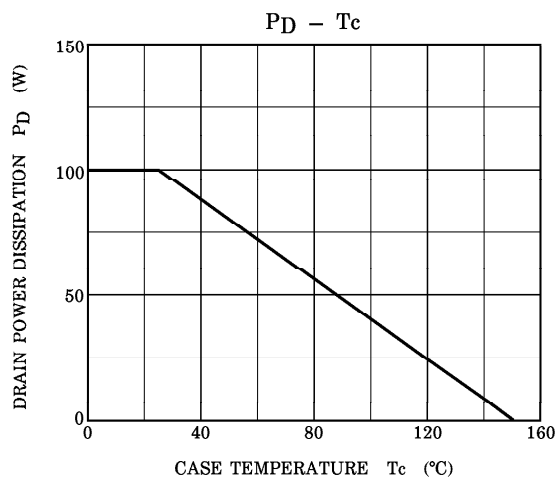
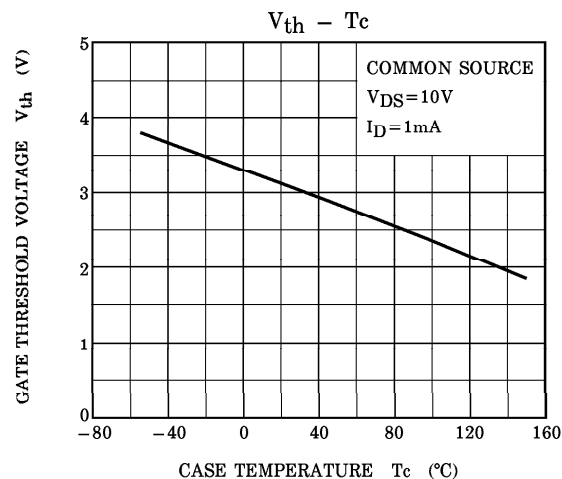
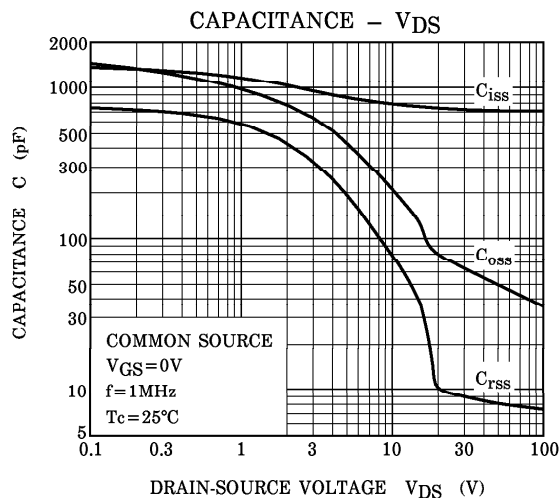
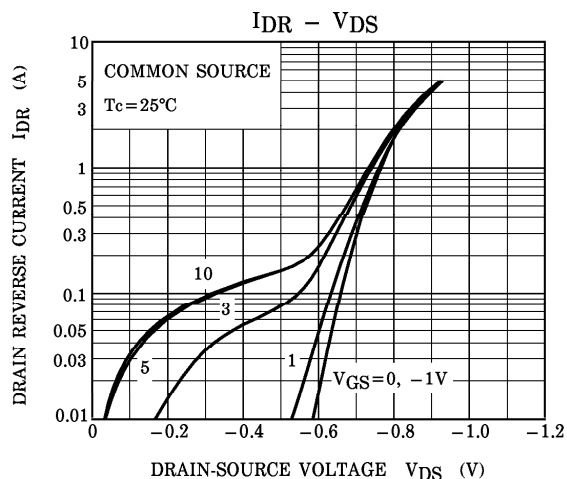
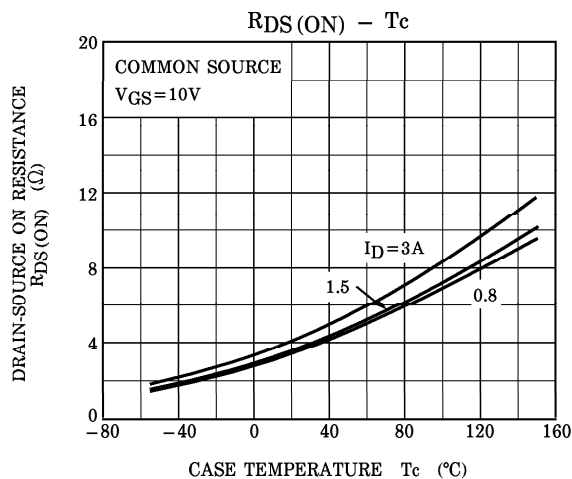
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

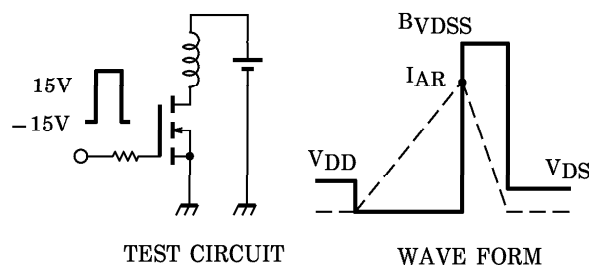
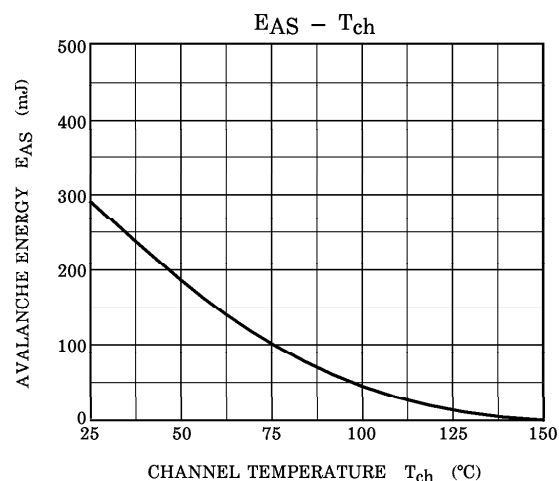
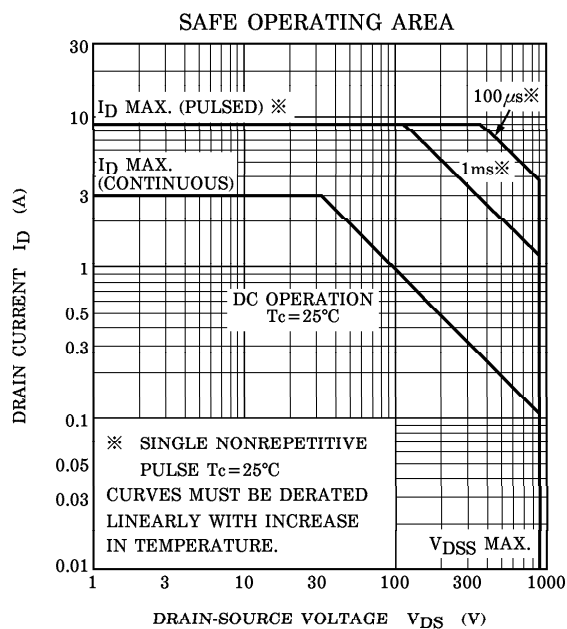
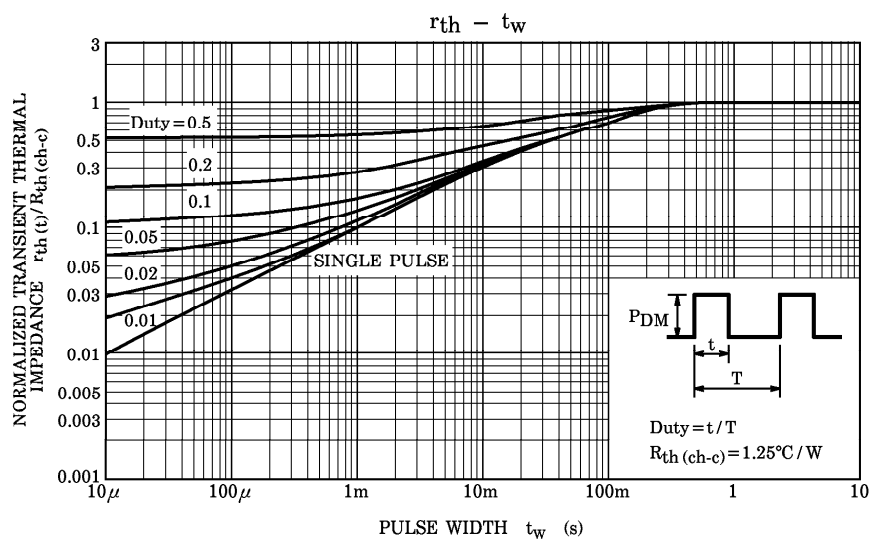
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	3	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	9	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = 3A, V_{GS} = 0V$	—	—	-1.9	V
Reverse Recovery Time	t_{rr}	$I_{DR} = 3A, V_{GS} = 0V$	—	1200	—	ns
Reverse Recovery Charge	Q_{rr}	$dI_{DR} / dt = 100A / \mu s$	—	8.5	—	μC

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Peak $I_{AR} = 3A$, $R_G = 25\Omega$
 $V_{DD} = 90V$, $L = 60mH$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{BVDSS}{BVDSS - V_{DD}} \right)$$